

HMC462LP5 / 462LP5E

v05.0213



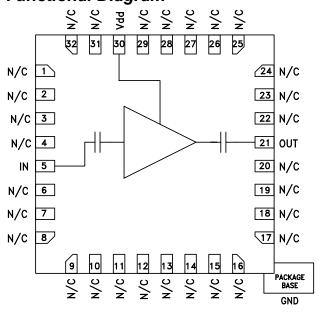
GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 2 - 20 GHz

Typical Applications

The HMC462LP5 / HMC462LP5E Wideband LNA is ideal for:

- Telecom Infrastructure
- Microwave Radio & VSAT
- Military EW, ECM & C³I
- Test Instrumentation
- Fiber Optics

Functional Diagram



Features

Noise Figure: 2.5 dB @ 10 GHz

Gain: 13 dB

P1dB Output Power: +14.5 dBm @ 10 GHz

Self-Biased: +5V @ 66mA 50 Ohm Matched Input/Output 25 mm² Leadless SMT Package

General Description

The HMC462LP5 & HMC462LP5E are GaAs MMIC pHEMT Low Noise Distributed Amplifiers in leadless 5x5 mm surface mount packages which operate between 2 and 20 GHz. The self-biased amplifier provides 13 dB of gain, 2.5 to 3.5 dB noise figure and +14.5 dBm of output power at 1 dB gain compression while requiring only 66 mA from a single +5V supply. Gain flatness is excellent from 6 - 18 GHz making the HMC462LP5 & HMC462LP5E ideal for EW, ECM RADAR and test equipment applications. The wideband amplifier I/Os are internally matched to 50 Ohms and are internally DC blocked.

Electrical Specifications, $T_A = +25^{\circ}$ C, Vdd=5V

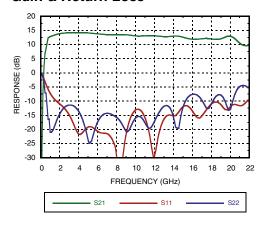
Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range		2 - 6			6 - 14			14 - 20		GHz
Gain	12	14		11	13		10	12		dB
Gain Flatness		±0.5			±0.5			±0.5		dB
Gain Variation Over Temperature		0.015	0.025		0.02	0.03		0.03	0.04	dB/ °C
Noise Figure		3.0	4.0		2.5	4.0		4.0	6.0	dB
Input Return Loss		15			13			11		dB
Output Return Loss		12			12			8		dB
Output Power for 1 dB Compression (P1dB)	12	15		11	14		9	12		dBm
Saturated Output Power (Psat)		17			16			15		dBm
Output Third Order Intercept (IP3)		26			25			22		dBm
Supply Current (Idd) (Vdd= 5V)	41	66	84	41	66	84	41	66	84	mA



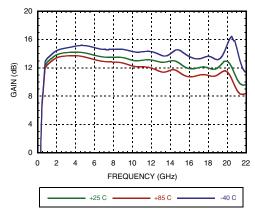


GAAS PHEMT MMIC LOW NOISE AMPLIFIER, 2 - 20 GHz

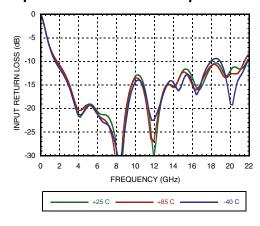
Gain & Return Loss



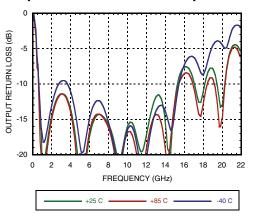
Gain vs. Temperature



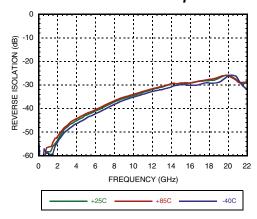
Input Return Loss vs. Temperature



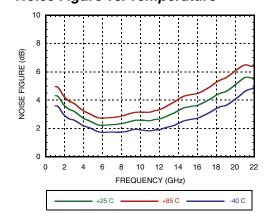
Output Return Loss vs. Temperature



Reverse Isolation vs. Temperature



Noise Figure vs. Temperature

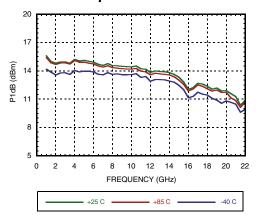




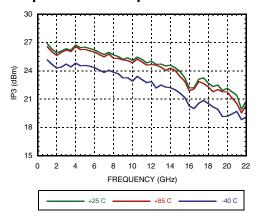


GAAS PHEMT MMIC LOW NOISE AMPLIFIER, 2 - 20 GHz

P1dB vs. Temperature



Output IP3 vs. Temperature

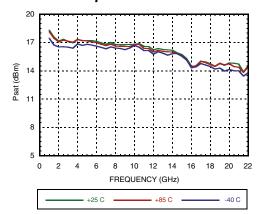


Absolute Maximum Ratings

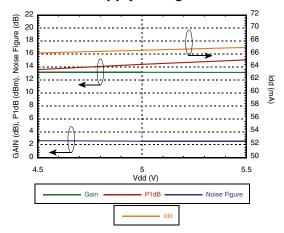
Drain Bias Voltage (Vdd)	+9 Vdc
RF Input Power (RFIN)(Vdd = +5 Vdc)	+18 dBm
Channel Temperature	150 °C
Continuous Pdiss (T = 85 °C) (derate 50 mW/°C above 85 °C)	3.25 W
Thermal Resistance (channel to ground paddle)	52 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C

ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

Psat vs. Temperature



Gain, Power, Noise Figure & Supply Current vs. Supply Voltage @ 10 GHz



Typical Supply Current vs. Vdd

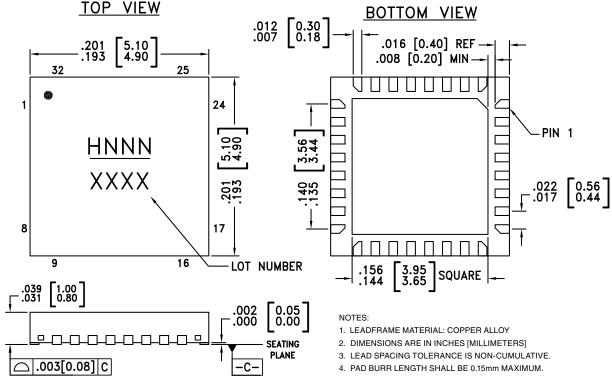
Vdd (V)	Idd (mA)
+4.5	66
+5.0	67
+5.5	68
+7.5	71
+8.0	72
+8.5	73





GAAS PHEMT MMIC LOW NOISE AMPLIFIER, 2 - 20 GHz

Outline Drawing



- PAD BURR HEIGHT SHALL BE 0.05mm MAXIMUM.
- 5. PACKAGE WARP SHALL NOT EXCEED 0.05mm.
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.
- 7. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [3]	
HMC462LP5	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 [1]	H462 XXXX	
HMC462LP5E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [2]	H462 XXXX	

- [1] Max peak reflow temperature of 235 °C
- [2] Max peak reflow temperature of 260 °C
- [3] 4-Digit lot number XXXX



HMC462LP5 / 462LP5E

v05.0213



GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 2 - 20 GHz

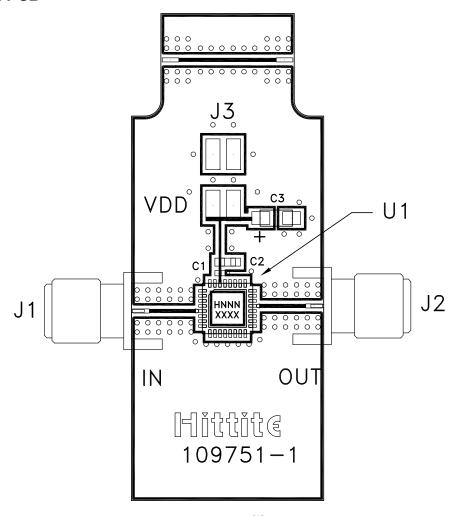
Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1 - 4, 6 - 20, 22 - 29, 31, 32	N/C	No connection. These pins may be connected to RF ground. Performance will not be affected.	
5	RFIN	This pad is AC coupled and matched to 50 Ohms.	RFIN ○──
21	RFOUT	This pad is AC coupled and matched to 50 Ohms.	— —○ RFOUT
30	Vdd	Power supply voltage for the amplifier. External bypass capacitors are required.	Vdd
Ground Paddle	GND	Ground paddle must be connected to RF/DC ground.	⊖ GND =



GAAS PHEMT MMIC LOW NOISE AMPLIFIER, 2 - 20 GHz

Evaluation PCB



List of Materials for Evaluation PCB 108338 [1]

Item	Description
J1 - J2	PCB Mount SMA Connector
J3	2 mm Molex Header
C1	100 pF Capacitor, 0402 Pkg.
C2	1000 pF Capacitor, 0603 Pkg.
C3	4.7 μF Capacitor, Tantalum
U1	HMC462LP5 / HMC462LP5E
PCB [2]	109751 Evaluation PCB

^[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for RF Development Tools category:

Click to view products by Analog Devices manufacturer:

Other Similar products are found below:

MAAM-011117 MAAP-015036-DIEEV2 EV1HMC1113LP5 EV1HMC6146BLC5A EV1HMC637ALP5 EVAL-ADG919EBZ ADL5363EVALZ LMV228SDEVAL SKYA21001-EVB SMP1331-085-EVB EV1HMC618ALP3 EVAL01-HMC1041LC4 MAAL-011111-000SMB
MAAM-009633-001SMB MASW-000936-001SMB 107712-HMC369LP3 107780-HMC322ALP4 SP000416870 EV1HMC470ALP3
EV1HMC520ALC4 EV1HMC244AG16 MAX2614EVKIT# 124694-HMC742ALP5 SC20ASATEA-8GB-STD MAX2837EVKIT+
MAX2612EVKIT# MAX2692EVKIT# EV1HMC629ALP4E SKY12343-364LF-EVB 108703-HMC452QS16G EV1HMC863ALC4
EV1HMC427ALP3E 119197-HMC658LP2 EV1HMC647ALP6 ADL5725-EVALZ 106815-HMC441LM1 EV1HMC1018ALP4
UXN14M9PE MAX2016EVKIT EV1HMC939ALP4 MAX2410EVKIT MAX2204EVKIT+ EV1HMC8073LP3D SIMSA868-DKL
SIMSA868C-DKL SKY65806-636EK1 SKY68020-11EK1 SKY67159-396EK1 SKY66181-11-EK1 SKY65804-696EK1